# Low-Voltage CMOS Quad 2-Input AND Gate

# With 5 V-Tolerant Inputs

The MC74LCX08 is a high performance, quad 2–input AND gate operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A  $V_{\rm I}$  specification of 5.5 V allows MC74LCX08 inputs to be safely driven from 5 V devices.

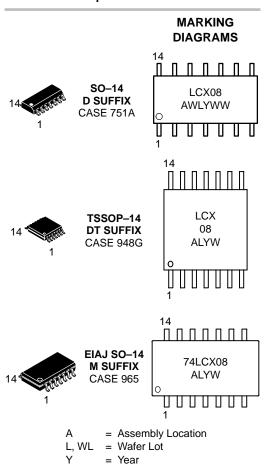
Current drive capability is 24 mA at the outputs.

- Designed for 2.3 V to 3.6 V V<sub>CC</sub> Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



## ON Semiconductor™

http://onsemi.com



#### ORDERING INFORMATION

W, WW = Work Week

Device	Package	Shipping
MC74LCX08D	SO-14	55 Units/Rail
MC74LCX08DR2	SO-14	2500 Units/Reel
MC74LCX08DT	TSSOP-14	96 Untis/Rail
MC74LCX08DTR2	TSSOP-14	2500 Units/Reel
MC74LCX08M	EIAJ SO-14	50 Units/Rail
MC74LCX08MEL	EIAJ SO-14	2000 Units/Reel

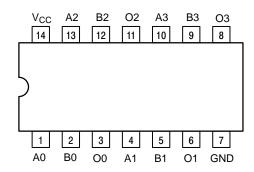


Figure 1. Pinout: 14-Lead (Top View)

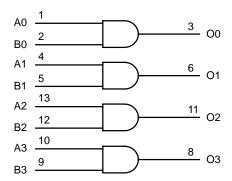


Figure 2. Logic Diagram

#### **PIN NAMES**

Pins	Function	
An, Bn	Data Inputs	
On	Outputs	

#### **TRUTH TABLE**

Inp	outs	Outputs
An	Bn	On
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

H = High Voltage Level L = Low Voltage Level

For  $I_{CC}$  reasons, DO NOT FLOAT Inputs

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1.)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
l <sub>OK</sub>	DC Output Diode Current	<b>-50</b>	V <sub>O</sub> < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
I <sub>O</sub>	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

<sup>1.</sup>  $I_O$  absolute maximum rating must be observed.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Туре	Max	Unit
V <sub>CC</sub>	,	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	٧
V <sub>O</sub>		(HIGH or LOW State) (3–State)	0		V <sub>CC</sub>	V
I <sub>OH</sub>		$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			-24 -12 -8	mA
I <sub>OL</sub>		$V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T <sub>A</sub>	Operating Free-Air Temperature		-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V <sub>IN</sub> from 0.	8 V to 2.0 V, V <sub>CC</sub> = 3.0 V	0		10	ns/V

#### DC ELECTRICAL CHARACTERISTICS

	Characteristic		T <sub>A</sub> = -40°C		
Symbol		Condition	Min	Max	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2.)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V	1.7		V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V	2.0		
V <sub>IL</sub>	LOW Level Input Voltage (Note 2.)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V		0.7	V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V		0.8	
V <sub>OH</sub>	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V <sub>CC</sub> - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		V <sub>CC</sub> = 2.7 V; I <sub>OH</sub> = -12 mA	2.2		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -18 mA	2.4		
		V <sub>CC</sub> = 3.0 V; I <sub>OH</sub> = -24 mA	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OL} = 100 \mu\text{A}$		0.2	V
		V <sub>CC</sub> = 2.3 V; I <sub>OL</sub> = 8 mA		0.6	
		V <sub>CC</sub> = 2.7 V; I <sub>OL</sub> = 12 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 16 mA		0.4	
		V <sub>CC</sub> = 3.0 V; I <sub>OL</sub> = 24 mA		0.55	
I <sub>I</sub>	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	
Δl <sub>CC</sub>	Increase in I <sub>CC</sub> per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

<sup>2.</sup> These values of  $V_I$  are used to test DC electrical characteristics only.

#### AC CHARACTERISTICS $t_R$ = $t_F$ = 2.5 ns; $R_L$ = 500 $\Omega$

				Limits					
				T <sub>A</sub> = -40°C to +85°C					
			V <sub>CC</sub> = 3.3	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 2.7 \text{ V}$ $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$					
			C <sub>L</sub> =	50 pF	C <sub>L</sub> =	50 pF	C <sub>L</sub> =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub>	Propagation Delay Time	1	1.5	5.5	1.5	6.2	1.5	6.6	ns
t <sub>PHL</sub>	Input to Output		1.5	5.5	1.5	6.2	1.5	6.6	
toshl	Output-to-Output Skew			1.0					ns
toslh	(Note 3.)			1.0					

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

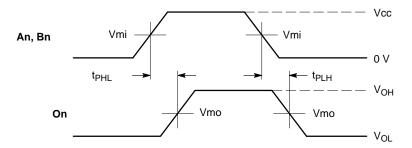
#### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V
	(Note 4.)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.6		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		-0.8		V
	(Note 4.)	$V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		-0.6		V

<sup>4.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Parameter Condition		Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF

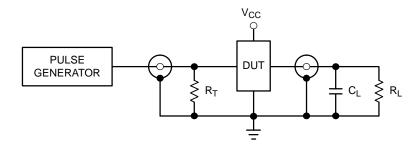


**WAVEFORM 1 – PROPAGATION DELAYS** 

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$ 

	Vcc					
Symbol	3.3 V <u>+</u> 0.3 V	2.7 V	2.5 V <u>+</u> 0.2 V			
Vmi	1.5 V	1.5 V	Vcc/2			
Vmo	1.5 V	1.5 V	Vcc/2			

Figure 3. AC Waveforms



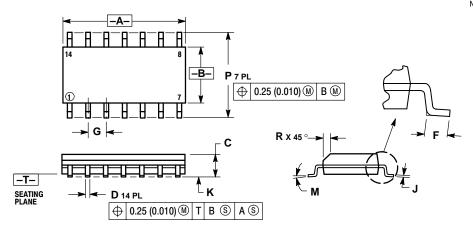
 $C_L=50$  pF at  $V_{CC}=3.3\pm0.3$  V or equivalent (includes jig and probe capacitance)  $C_L=30$  pF at  $V_{CC}=2.5\pm0.2$  V or equivalent (includes jig and probe capacitance)  $R_L=R_1=500~\Omega$  or equivalent

 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

#### **PACKAGE DIMENSIONS**

#### SO-14 **D SUFFIX** CASE 751A-03 ISSUE F



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 114-5M, 1982.

  CONTROLLING DIMENSION: MILLIMETER.

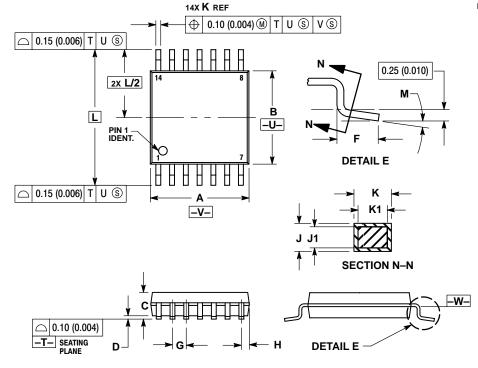
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  MAINIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.

  5. DIMENSION D DOES NOT INCLUDE DAMBAR DIMENSION D DUES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES				
DIM	MIN MAX		MIN	MAX			
Α	8.55	8.75	0.337	0.344			
В	3.80	4.00	0.150	0.157			
С	1.35	1.75	0.054	0.068			
D	0.35	0.49	0.014	0.019			
F	0.40	1.25	0.016	0.049			
G	1.27	BSC	0.050 BSC				
J	0.19	0.25	0.008	0.009			
K	0.10	0.25	0.004	0.009			
M	0°	7°	0 °	7°			
P	5.80	6.20	0.228	0.244			
R	0.25	0.50	0.010	0.019			

#### TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE O**

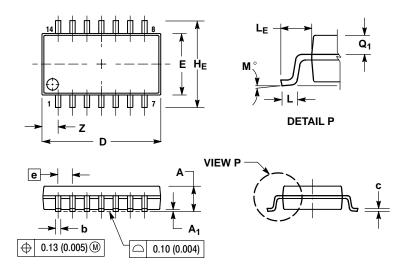


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- OR GATE BOHRAS SHALL NOT EXCEED 0.15
  (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD
  FLASH OR PROTRUSION. INTERLEAD FLASH OR
  PROTRUSION SHALL NOT EXCEED
  0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN
  EXCESS OF THE K DIMENSION AT MAXIMUM
  MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0 °	8°	0 °	8 °	

#### **PACKAGE DIMENSIONS**

EIAJ SO-14 **M SUFFIX** CASE 965-01 **ISSUE O** 



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018). TO BE 0.46 ( 0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q	0.70	0.90	0.028	0.035
Z		1.42		0.056

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